

HZ Series

Silicon Epitaxial Planar Zener Diode for Stabilized Power Supply

HITACHI

ADE-208-117B(Z)
Rev 2
Nov 1999

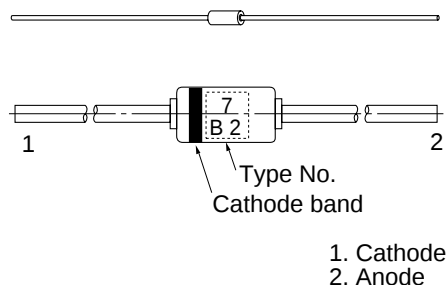
Features

- Low leakage, low zener impedance and maximum power dissipation of 500 mW are ideally suited for stabilized power supply, etc.
- Wide spectrum from 1.6V through 38V of zener voltage provide flexible application.

Ordering Information

Type No.	Mark	Package Code
HZ Series	Type No.	DO-35

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd	500	mW
Junction temperature	Tj	175	°C
Storage temperature	Tstg	-55 to +175	°C

Electrical Characteristics (Ta = 25°C)

Type	Grade	Zener Voltage		Test Condition	Reverse Current		Dynamic Resistance	
		V _Z (V)*1			I _R (μA)	Test Condition	r _d (Ω)	Test Condition
		Min	Max	I _Z (mA)	Max	V _R (V)	Max	I _Z (mA)
HZ2	A1	1.6	1.8	5	25	0.5	100	5
	A2	1.7	1.9					
	A3	1.8	2.0					
	B1	1.9	2.1	5	5	0.5	100	5
	B2	2.0	2.2					
	B3	2.1	2.3					
	C1	2.2	2.4					
	C2	2.3	2.5					
	C3	2.4	2.6					
HZ3	A1	2.5	2.7	5	5	0.5	100	5
	A2	2.6	2.8					
	A3	2.7	2.9					
	B1	2.8	3.0					
	B2	2.9	3.1					
	B3	3.0	3.2					
	C1	3.1	3.3					
	C2	3.2	3.4					
	C3	3.3	3.5					
HZ4	A1	3.4	3.6	5	5	1.0	100	5
	A2	3.5	3.7					
	A3	3.6	3.8					

Note: 1. Tested with DC.

Type	Grade	Zener Voltage		Reverse Current		Dynamic Resistance	
		V _Z (V)*1		Test Condition	I _R (μA)	Test Condition	r _d (Ω)
		Min	Max	I _Z (mA)	Max	V _R (V)	Max
HZ4	B1	3.7	3.9	5	5	1.0	100
	B2	3.8	4.0				
	B3	3.9	4.1				
	C1	4.0	4.2				
	C2	4.1	4.3				
	C3	4.2	4.4				
HZ5	A1	4.3	4.5	5	5	1.5	100
	A2	4.4	4.6				
	A3	4.5	4.7				
	B1	4.6	4.8				
	B2	4.7	4.9				
	B3	4.8	5.0				
	C1	4.9	5.1				
	C2	5.0	5.2				
	C3	5.1	5.3				
HZ6	A1	5.2	5.5	5	5	2.0	40
	A2	5.3	5.6				
	A3	5.4	5.7				
	B1	5.5	5.8				
	B2	5.6	5.9				
	B3	5.7	6.0				
	C1	5.8	6.1				
	C2	6.0	6.3				
	C3	6.1	6.4				
HZ7	A1	6.3	6.6	5	1	3.5	15
	A2	6.4	6.7				
	A3	6.6	6.9				
	B1	6.7	7.0				
	B2	6.9	7.2				
	B3	7.0	7.3				

Note: 1. Tested with DC.

HZ Series

		Zener Voltage		Reverse Current		Dynamic Resistance	
		V _z (V)*1		Test Condition	I _R (μA)	Test Condition	
Type	Grade	Min	Max	I _z (mA)	Max	V _R (V)	Max
HZ7	C1	7.2	7.6	5	1	3.5	15
	C2	7.3	7.7				
	C3	7.5	7.9				
HZ9	A1	7.7	8.1	5	1	5.0	20
	A2	7.9	8.3				
	A3	8.1	8.5				
	B1	8.3	8.7				
	B2	8.5	8.9				
	B3	8.7	9.1				
	C1	8.9	9.3				
	C2	9.1	9.5				
	C3	9.3	9.7				
HZ11	A1	9.5	9.9	5	1	7.5	25
	A2	9.7	10.1				
	A3	9.9	10.3				
	B1	10.2	10.6				
	B2	10.4	10.8				
	B3	10.7	11.1				
	C1	10.9	11.3				
	C2	11.1	11.6				
	C3	11.4	11.9				
HZ12	A1	11.6	12.1	5	1	9.5	35
	A2	11.9	12.4				
	A3	12.2	12.7				
	B1	12.4	12.9				
	B2	12.6	13.1				
	B3	12.9	13.4				
	C1	13.2	13.7				
	C2	13.5	14.0				
	C3	13.8	14.3				

Note: 1. Tested with DC.

		Zener Voltage		Reverse Current		Dynamic Resistance		
		V_z (V)* ¹		Test Condition	I_R (μA)	Test Condition	r_d (Ω)	Test Condition
Type	Grade	Min	Max	I_z (mA)	Max	V_R (V)	Max	I_z (mA)
HZ15	1	14.1	14.7	5	1	11.0	40	5
	2	14.5	15.1					
	3	14.9	15.5					
HZ16	1	15.3	15.9	5	1	12.0	45	5
	2	15.7	16.5					
	3	16.3	17.1					
HZ18	1	16.9	17.7	5	1	13.0	55	5
	2	17.5	18.3					
	3	18.1	19.0					
HZ20	1	18.8	19.7	2	1	15.0	60	2
	2	19.5	20.4					
	3	20.2	21.1					
HZ22	1	20.9	21.9	2	1	17.0	65	2
	2	21.6	22.6					
	3	22.3	23.3					
HZ24	1	22.9	24.0	2	1	19.0	70	2
	2	23.6	24.7					
	3	24.3	25.5					
HZ27	1	25.2	26.6	2	1	21.0	80	2
	2	26.2	27.6					
	3	27.2	28.6					
HZ30	1	28.2	29.6	2	1	23.0	100	2
	2	29.2	30.6					
	3	30.2	31.6					
HZ33	1	31.2	32.6	2	1	25.0	120	2
	2	32.2	33.6					
	3	33.2	34.6					
HZ36	1	34.2	35.7	2	1	27.0	140	2
	2	35.3	36.8					
	3	36.4	38.0					

Note: 1. Tested with DC.

Note: 2. Type No. is as follows; HZ2B1, HZ2B2, HZ36-3.

Main Characteristic

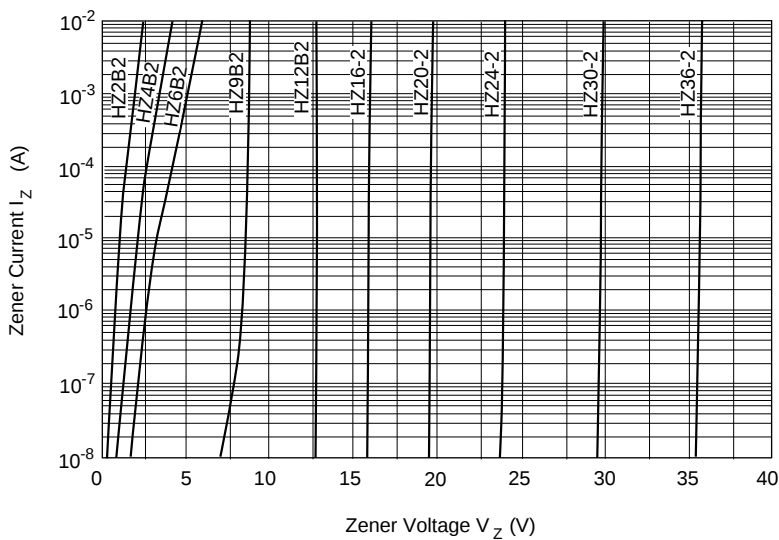


Fig.1 Zener current Vs. Zener voltage

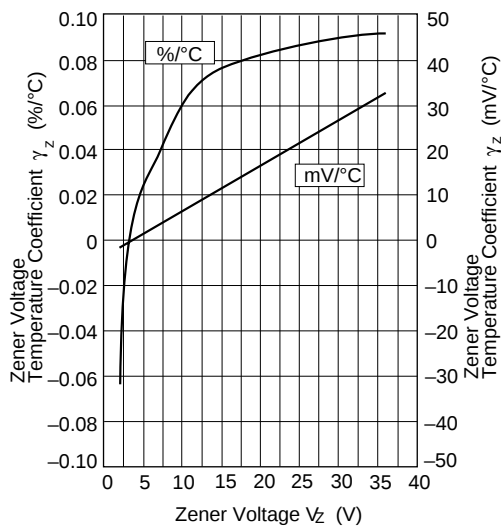


Fig.2 Temperature Coefficient Vs. Zener voltage

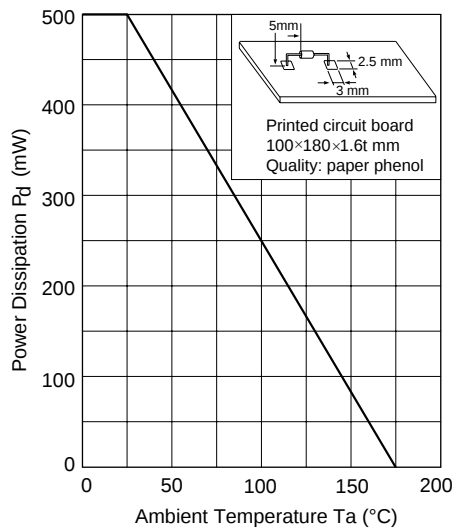
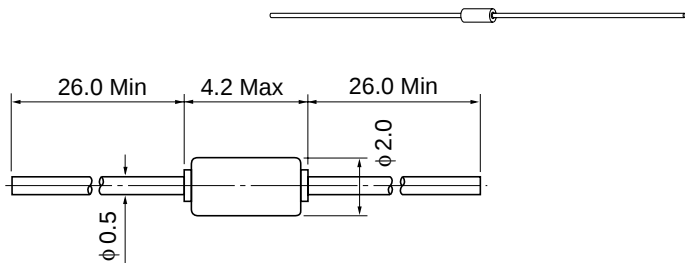


Fig.3 Power Dissipation Vs. Ambient Temperature

Package Dimensions

Unit: mm



Hitachi Code	DO-35
JEDEC	Conforms
EIAJ	Conforms
Mass	0.13 g

Cautions

1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
 2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
 3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
 4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
 5. This product is not designed to be radiation resistant.
 6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
 7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: http://semiconductor.hitachi.com/
	Europe	: http://www.hitachi-eu.com/hel/ecg
	Asia (Singapore)	: http://www.has.hitachi.com.sg/grp3/sicd/index.htm
	Asia (Taiwan)	: http://www.hitachi.com.tw/E/Product/SICD_Frame.htm
	Asia (HongKong)	: http://www.hitachi.com.hk/eng/bo/grp3/index.htm
	Japan	: http://www.hitachi.co.jp/Sicd/indx.htm

For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322
--	---

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

Copyright ' Hitachi, Ltd., 1999. All rights reserved. Printed in Japan.